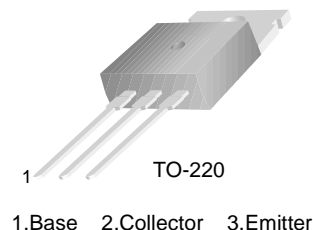


■ ■ APPLICATION: Medium Power Linear Switching Applications.

■ ■ MAXIMUM RATINGS (Ta=25°C)

PARAMETER	SYMBOL	RATING	UNIT
Collector-base voltage	V _{CBO}	-100	V
Collector-emitter voltage	V _{CEO}	-100	V
Emitter-base voltage	V _{EBO}	-5	V
Collector current	I _C	-3	A
Base current	I _B	-3	A
Collector Power Dissipation (Ta=25°C)	P _C	2	W
Collector Power Dissipation (Tc=25°C)	P _C	40	W
Junction Temperature	T _J	150	°C
Storage Temperature Range	T _{stg}	-65~150	°C



■ ■ ELECTRICAL CHARACTERISTICS

(Ta=25°C)

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	TEST CONDITION
DC Current Gain	h _{FE1}	10		50		V _{CE} = -4V, I _C = -3A
	h _{FE2}	25				V _{CE} = -4V, I _C = -1A
Collector-Emitter Cut-off Current	I _{CEO}			-0.3	mA	V _{CE} =-60V, I _E =0
Emitter-Base Cut-off Current	I _{EBO}			-1	mA	V _{EB} =-5V, I _C =0
Collector-Base Breakdown Voltage	BV _{CBO}	-100			V	I _C = -1mA, I _E =0
Base-Emitter on Voltage	BV _{CEO}	-100			V	I _C = -30mA, I _B =0
Emitter-Base Breakdown Voltage	BV _{EBO}	-5			V	I _E = -1mA, I _C =0
Base-Emitter on Voltage	V _{BE(on)}			-1.8	V	V _{CE} = -4V, I _C = -3A
Collector-Emitter Saturation Voltage	V _{CE(sat)}			-1.2	V	I _C = -3A, I _B =-0.375A
Gain bandwidth product	f _T	3			MHz	V _{CE} =-10V, I _C =-0.5A, f=1MHz

■ ■ h_{FE} Classification And Marking

Mark	TIP32C
Classification	
h _{FE}	10~50